

ABSTRACT OF THE DISCLOSURE

In a p-type base layer of a trench IGBT comprising a p-type collector layer, an n-type base layer formed on the p-type collector layer, the p-type base layer formed on the n-type base layer, and an n-type emitter layer formed on the surface of the p-type base layer, the point of the highest impurity concentration is located closer to the n-type base layer than the junction with the emitter layer. In other words, the pinch-off of the channel is generated in the position closer to the n-type base layer than to the junction between the p-type base layer and the n-type emitter layer.